

GaAs-IR-Lumineszenzdiode

GaAs Infrared Emitter

LD 271
LD 271 H
LD 271 L
LD 271 HL



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gehäusegleich mit SFH 300, SFH 203

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken

Features

- Very highly efficient GaAs-LED
- High reliability
- Spectral match with silicon photodetectors
- Same package as SFH 300, SFH 203

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
LD 271	Q62703-Q148	5-mm-LED-Gehäuse (T 1 ³ / ₄), graugetöntes Epoxy-Gießharz, Lötspieße im 2.54-mm-Raster (¹ / ₁₀ " 5 mm LED package (T 1 ³ / ₄), grey colored epoxy resin lens, solder tabs lead spacing 2.54 mm (¹ / ₁₀ "
LD 271 L	Q62703-Q833	
LD 271 H	Q62703-Q256	
LD 271 HL	Q62703-Q838	

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlaßstrom Forward current	I_F	130	mA
Stoßstrom, $t_p = 10 \mu s, D = 0$ Surge current	I_{FSM}	3.5	A
Verlustleistung Power dissipation	P_{tot}	220	mW
Wärmewiderstand Thermal resistance	R_{thJA}	330	K/W

Kennwerte ($T_A = 25 \text{ °C}$)
Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100 \text{ mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 25	Grad deg.
Aktive Chipfläche Active chip area	A	0.25	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.5×0.5	mm
Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top	H	4.0 ... 4.6	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100 \text{ mA}, R_L = 50 \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100 \text{ mA}, R_L = 50 \Omega$	t_r, t_f	1	μs

Kennwerte ($T_A = 25\text{ °C}$)
Characteristics (cont'd)

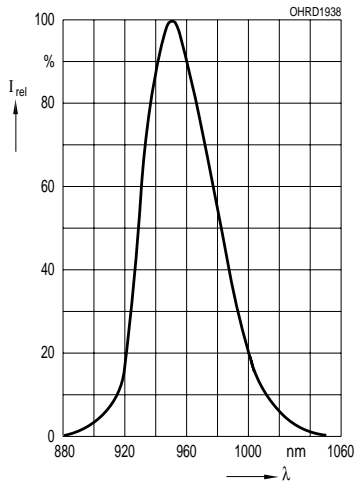
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität, $V_R = 0\text{ V}, f = 1\text{ MHz}$ Capacitance	C_o	40	pF
Durchlaßspannung Forward voltage $I_F = 100\text{ mA}, t_p = 20\text{ ms}$ $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.30 (≤ 1.5) 1.90 (≤ 2.5)	V V
Sperrstrom, $V_R = 5\text{ V}$ Reverse current	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluß Total radiant flux $I_F = 100\text{ mA}, t_p = 20\text{ ms}$	Φ_e	18	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.55	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	0.3	nm/K

Gruppierung der Strahlstärke I_e in Achsrichtung
gemessen bei einem Raumwinkel $\Omega = 0.01\text{ sr}$
Grouping of Radiant Intensity I_e in Axial Direction
at a solid angle of $\Omega = 0.01\text{ sr}$

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		LD 271 LD 271 L	LD 271 H LD 271 HL	
Strahlstärke Radiant intensity $I_F = 100\text{ mA}, t_p = 20\text{ ms}$ $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	I_e $I_{e\text{ typ.}}$	15 (≥ 10) 120	> 16	mW/sr mW/sr

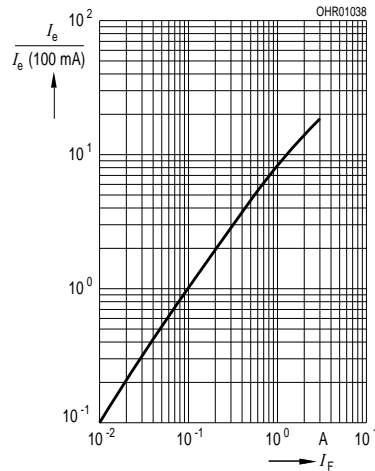
Relative Spectral emission

$I_{rel} = f(\lambda)$



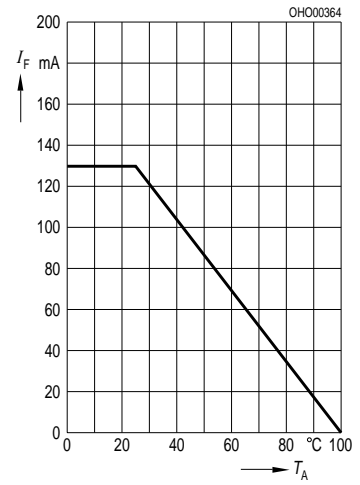
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$



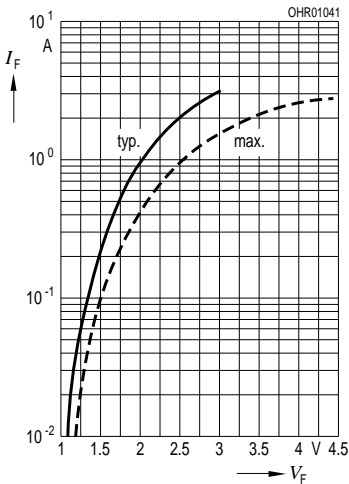
Max. Permissible Forward Current

$I_F = f(T_A)$

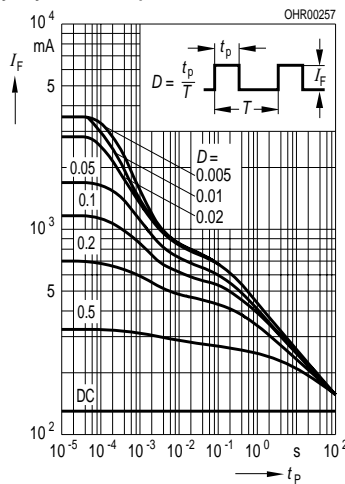


Forward Current

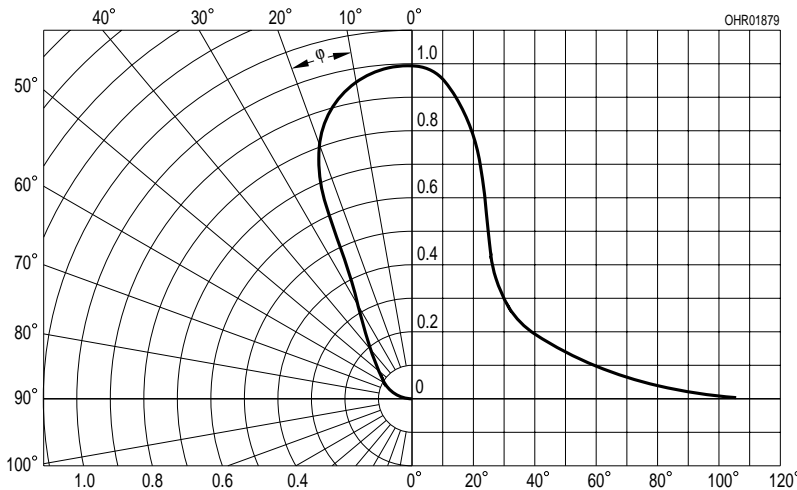
$I_F = f(V_F)$, single pulse, $t_p = 20 \mu\text{s}$



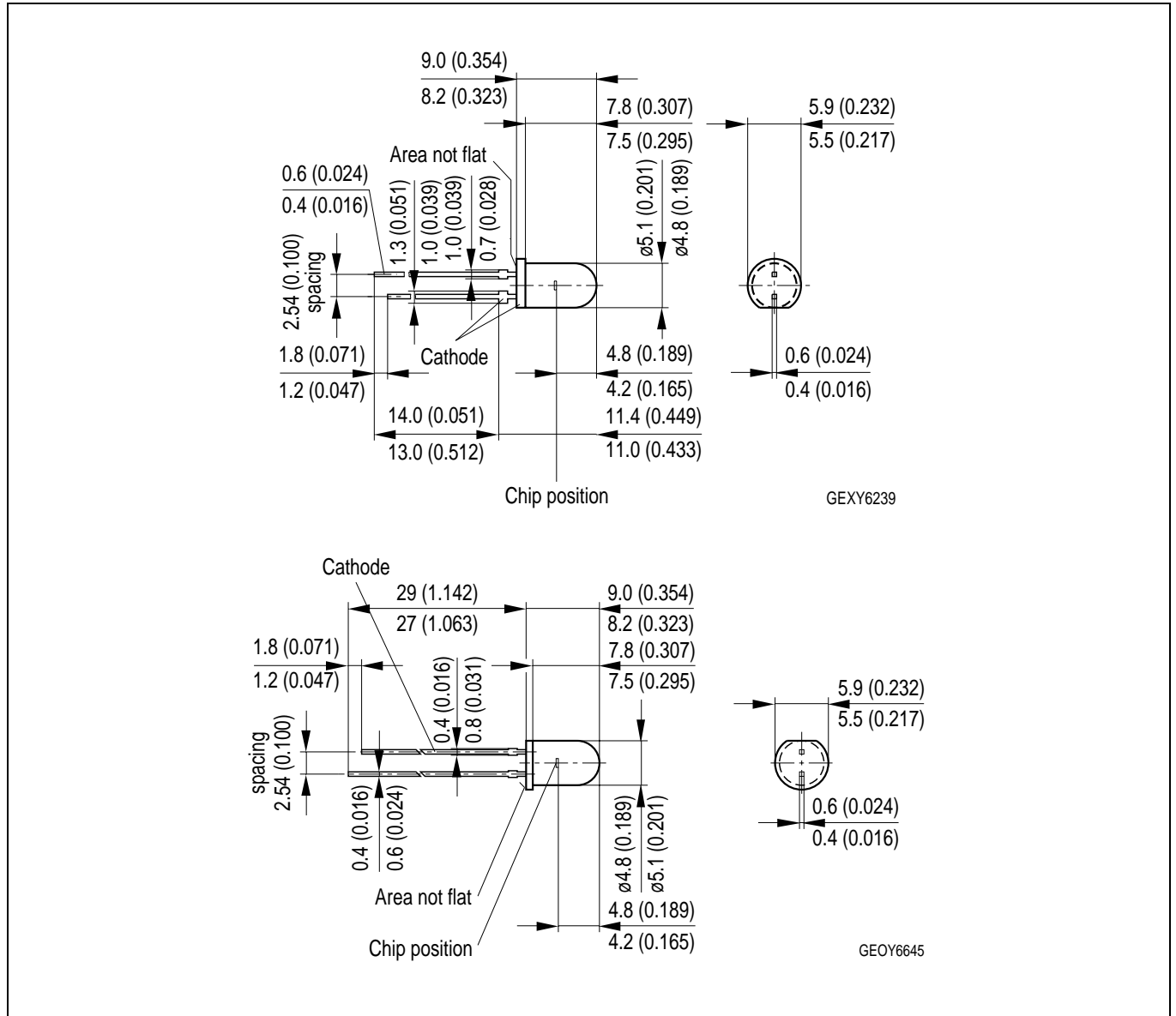
Permissible Pulse Handling Capability $I_F = f(\tau)$, $T_C = 25^\circ\text{C}$, duty cycle $D = \text{parameter}$



Radiation Characteristics $I_{rel} = f(\varphi)$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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